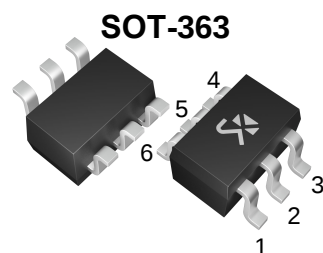
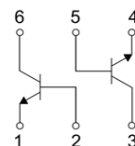


NPN+NPN Silicon Epitaxial Planar Transistor

Features

- Epitaxial Planar Die Construction
- Ideal for Low Power Amplification and Switching

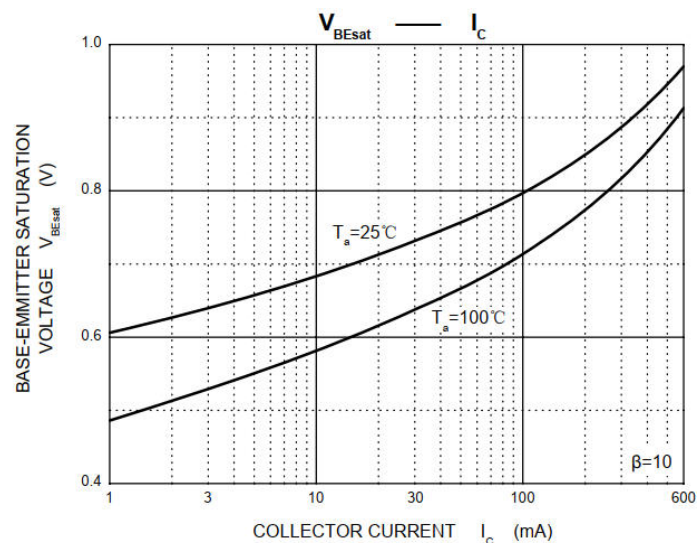
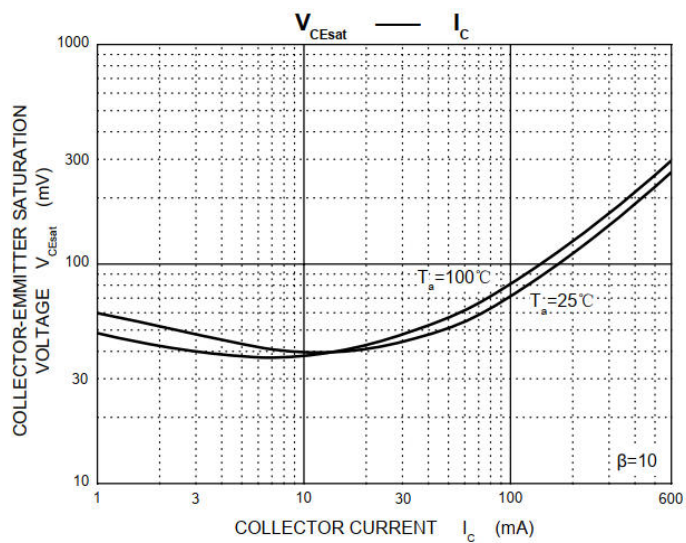
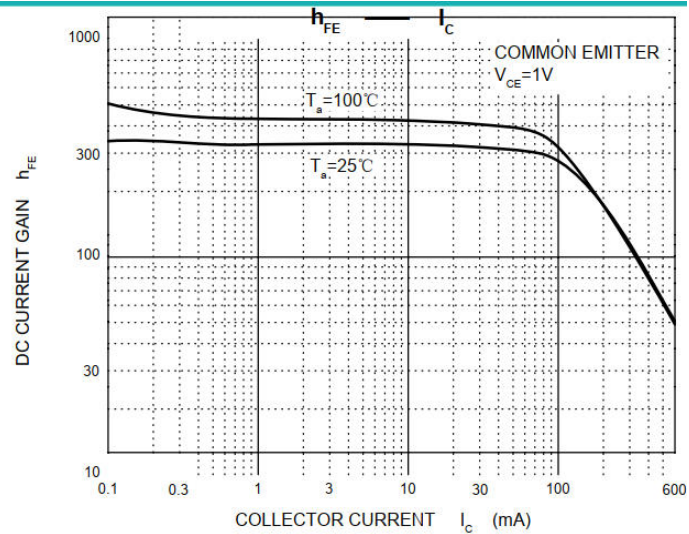
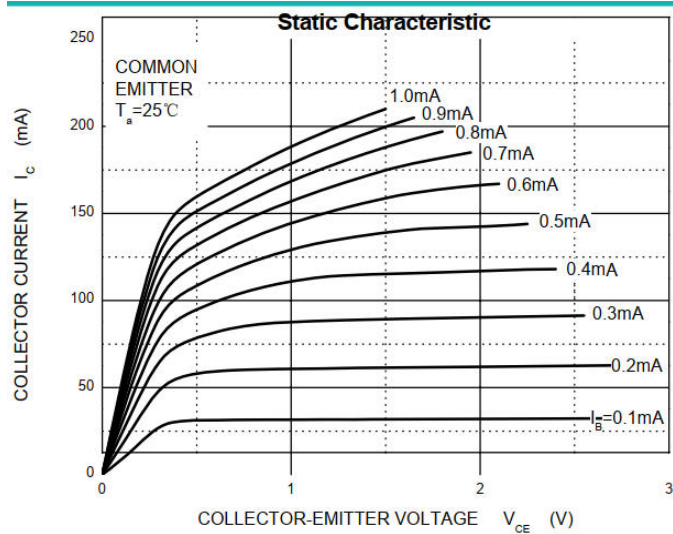


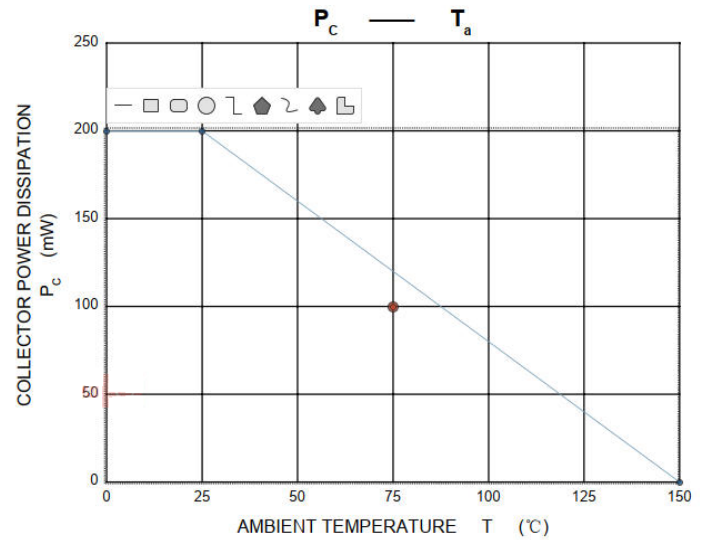
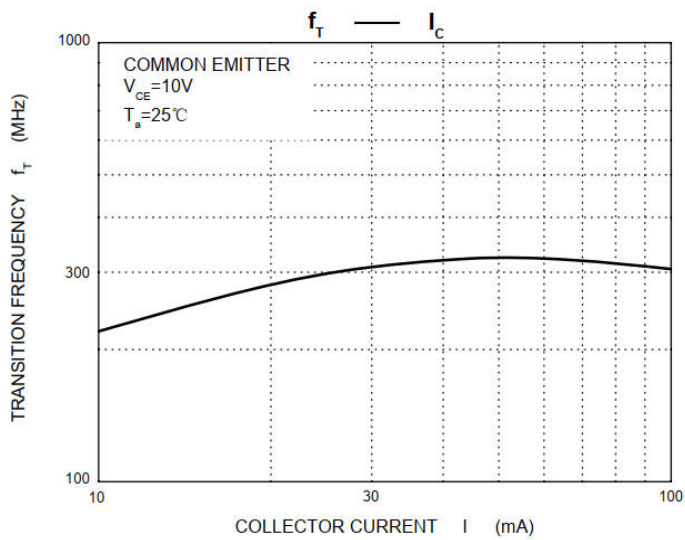
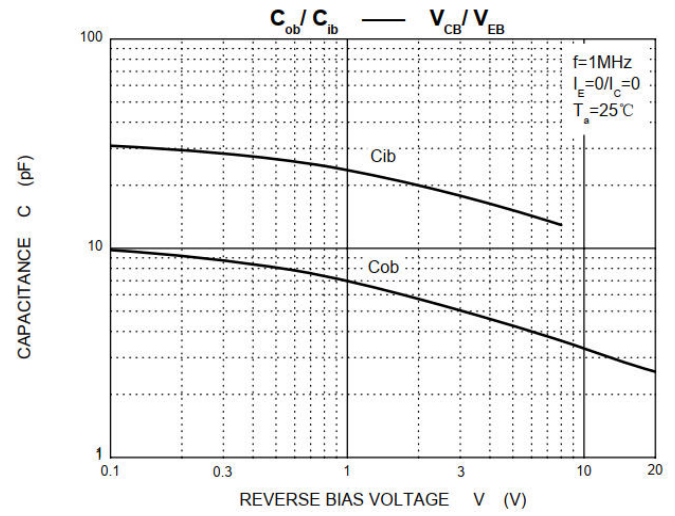
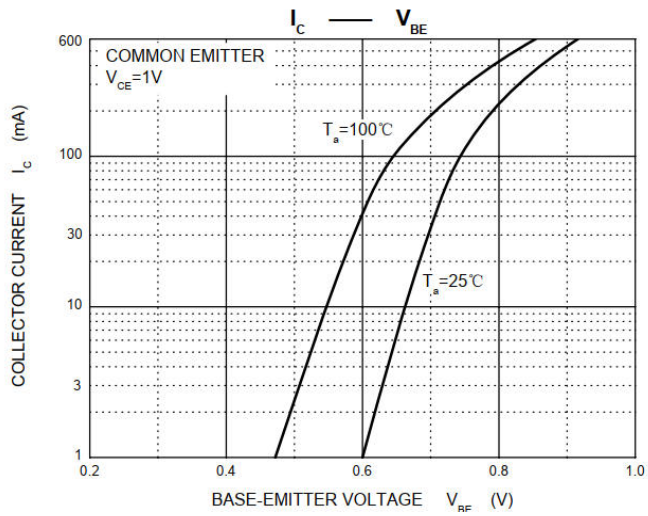
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	60	V
V_{CEO}	Collector-Emitter Voltage	40	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current -Continuous	600	mA
P_C	Collector Power Dissipation	200	mW
T_j	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55 to +150	$^{\circ}\text{C}$
$R_{\theta JA}$	Thermal Resistance Junction to Ambient	625	$^{\circ}\text{C}/\text{W}$

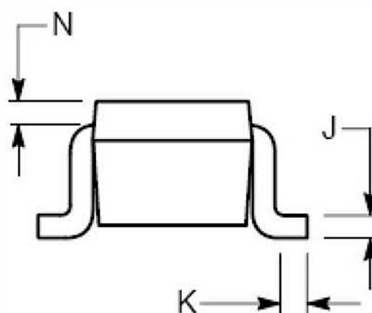
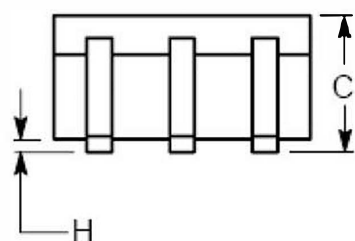
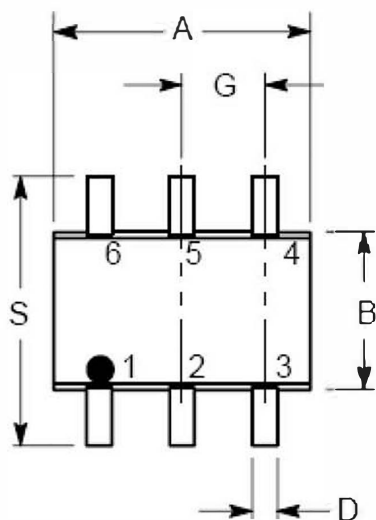
ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu\text{A}$, $I_E=0$	60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1\text{mA}$, $I_B=0$	40			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=10\mu\text{A}$, $I_C=0$	6			V
Collector cut-off current	I_{CBO}	$V_{CB}=50\text{V}$, $I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}$, $I_C=0$			0.1	μA
Collector cut-off current	I_{CEO}	$V_{CE}=35\text{V}$, $I_B=0$			0.5	μA
DC current gain	h_{FE}	$V_{CE}=1\text{V}$, $I_C=0.1\text{mA}$	20			
DC current gain	h_{FE}	$V_{CE}=1\text{V}$, $I_C=1\text{mA}$	40			
DC current gain	h_{FE}	$V_{CE}=1\text{V}$, $I_C=10\text{mA}$	80			
DC current gain	h_{FE}	$V_{CE}=1\text{V}$, $I_C=150\text{mA}$	100		300	
DC current gain	h_{FE}	$V_{CE}=2\text{V}$, $I_C=500\text{mA}$	40			
Collector-emitter saturation voltage	$V_{CE(Sat)}$	$I_C=150\text{mA}$, $I_B=15\text{mA}$			0.4	V
Collector-emitter saturation voltage	$V_{CE(Sat)}$	$I_C=500\text{mA}$, $I_B=50\text{mA}$			0.75	V
Base-emitter saturation voltage	$V_{BE(Sat)}$	$I_C=150\text{mA}$, $I_B=15\text{mA}$	0.75		0.95	V
Base-emitter saturation voltage	$V_{BE(Sat)}$	$I_C=500\text{mA}$, $I_B=50\text{mA}$			1.2	V
Transition frequency	f_T	$V_{CE}=10\text{V}$, $I_C=10\text{mA}$, $f=100\text{MHz}$	250			MHz
Collector output capacitance	C_{ob}	$V_{CB}=5\text{V}$, $I_E=0$, $f=1\text{MHz}$			6.5	pF





SOT-363 Outline Dimension



Symbol	Dimension In Millime/ers	
	Min	Max.
A	1.89	2.20
B	1.15	1.35
C	0.80	1.10
D	0.10	0.30
G	0.65 BSC	
H	---	0.10
J	0.10	0.25
K	0.10	0.30
N	0.20 REF	
S	2.00	2.20